

OM SENI

NUP3105LT1G ESD Protection Diode

Dual Line CAN Bus Protector

The SZ/NUP3105L has been designed to protect the CAN transceiver in 24 V systems from ESD and other harmful transient voltage events. This device provides bidirectional protection for each data line with a single compact SOT-23 package, giving the system designer a low cost option for improving system reliability and meeting stringent EMI requirements.

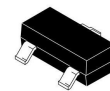
Features

- 350 W Peak Power Dissipation per Line (8/20 μ sec Waveform)
- Low Reverse Leakage Current (< 100 nA)
- Low Capacitance High-Speed CAN Data Rates
- IEC Compatibility:
 - IEC 61000-4-2 (ESD): Level 4
 - IEC 61000-4-4 (EFT): 50 A – 5/50 ns
 - IEC 61000-4-5 (Lighting) 8.0 A (8/20 μ s)
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

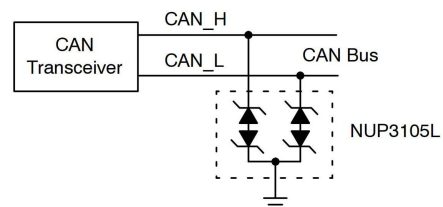
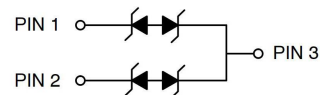
Applications

- Industrial Control Networks
 - ♦ Smart Distribution Systems (SDS[®])
 - ♦ DeviceNet[™]
- Automotive Networks
 - ♦ Low and High-Speed CAN
 - ♦ Fault Tolerant CAN
 - ♦ Trucks

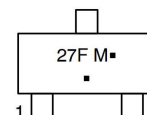
SOT-23 DUAL BIDIRECTIONAL VOLTAGE SUPPRESSOR 350 W PEAK POWER



SOT-23
CASE 318
STYLE 27



MARKING DIAGRAM



27F = Device Code
M = Date Code
▪ = Pb-Free Package

(Note: Microdot may be in either location)

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MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$, unless otherwise specified)

Symbol	Rating	Value	Unit
PPK	Peak Power Dissipation 8 x 20 μs Double Exponential Waveform (Note 1)	350	W
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_L	Lead Solder Temperature (10 s)	260	$^\circ\text{C}$
ESD	Human Body model (HBM) Machine Model (MM) IEC 61000-4-2 Specification (Contact)	8.0 400 30	kV V kV

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Non-repetitive current pulse per Figure 1.

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$, unless otherwise specified)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
V_{RWM}	Reverse Working Voltage	(Note 2)	–	–	32	V
V_{BR}	Breakdown Voltage	$I_T = 1\text{ mA}$ (Note 3)	35.6	–	–	V
I_R	Reverse Leakage Current	$V_{RWM} = 32\text{ V}$	–	–	100	nA
V_C	Clamping Voltage	$I_{PP} = 5\text{ A}$ (8/20 μs Waveform) (Note 4)	–	–	59	V
V_C	Clamping Voltage	$I_{PP} = 8\text{ A}$ (8/20 μs Waveform) (Note 4)	–	–	66	V
I_{PP}	Maximum Peak Pulse Current	8/20 μs Waveform (Note 4)	–	–	8.0	A
CJ	Capacitance	$V_R = 0\text{ V}$, $f = 1\text{ MHz}$ (Line to GND)	–	–	30	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

- Surge protection devices are normally selected according to the working peak reverse voltage (V_{RWM}), which should be equal or greater than the DC or continuous peak operating voltage level.
- V_{BR} is measured at pulse test current I_T .
- Pulse waveform per Figure 1.

TYPICAL PERFORMANCE CURVES

($T_J = 25^\circ\text{C}$ unless otherwise noted)

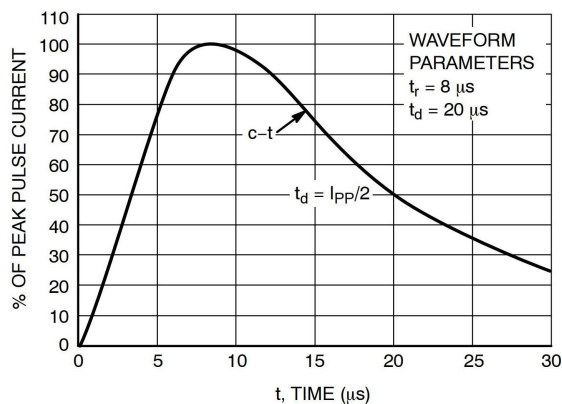


Figure 1. Pulse Waveform, 8/20 μs

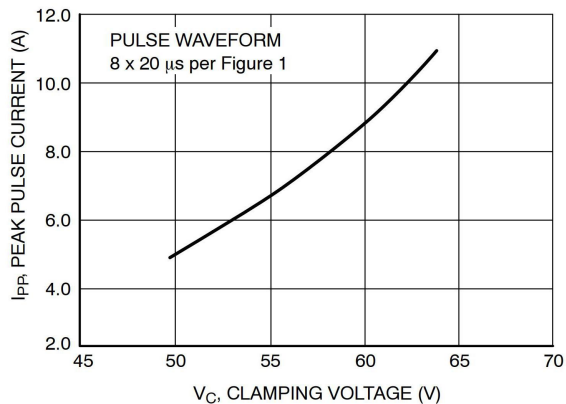


Figure 2. Clamping Voltage vs Peak Pulse Current

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Surge Protection Diode Protection Circuit

Surge protection diodes provide protection to a transceiver by clamping a surge voltage to a safe level. surge protection diodes have high impedance below and low impedance above their breakdown voltage. A surge protection Zener diode has its junction optimized to absorb the high peak energy of a transient event, while a standard Zener diode is designed and specified to clamp a steady state voltage.

Figure 3 provides an example of a dual bidirectional surge protection diode array that can be used for protection with the high-speed CAN network. The bidirectional array is created from four identical Zener surge protection diodes. The clamping voltage of the composite device is equal to the

breakdown voltage of the diode that is reversed biased, plus the diode drop of the second diode that is forward biased.

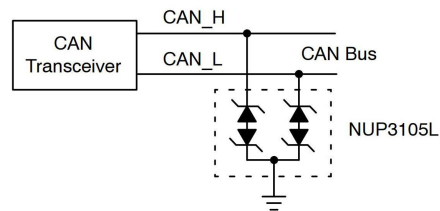


Figure 3. High-Speed and Fault Tolerant CAN Surge Protection Circuit

ORDERING INFORMATION

Device	Package	Shipping [†]
NUP3105LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
SZNUP3105LT1G*	SOT-23 (Pb-Free)	3,000 / Tape & Reel
NUP3105LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel
SZNUP3105LT3G*	SOT-23 (Pb-Free)	10,000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*SZ Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

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Ordering Information

PACKAGE	PACKAGE CODE	UNIT WEIGHT(g)	REEL(pcs)	BOX(pcs)	CARTON(pcs)	DELIVERY MODE
SOT-23	R1	0.008	3000	30000	240000	7"

Package Outline Dimensions (SOT-23)

Symbol	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	0.90	1.15	0.035	0.045
A1	-	0.10	-	0.004
A2	0.90	1.05	0.035	0.041
b	0.30	0.50	0.012	0.020
c	0.10	0.20	0.004	0.008
D	2.80	3.00	0.110	0.118
E	1.20	1.40	0.047	0.055
E1	2.25	2.55	0.089	0.100
e	0.950TYP		0.037TYP	
e1	1.80	2.00	0.071	0.079
L	0.550REF		0.022REF	
L1	0.30	0.50	0.012	0.020
θ	-	8°	-	8°

Suggested Pad Layout

Symbol	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
J	0.75	0.85	0.030	0.033
K	0.85	0.95	0.033	0.037
M	1.95	2.05	0.077	0.081
N	1.85	1.95	0.073	0.077